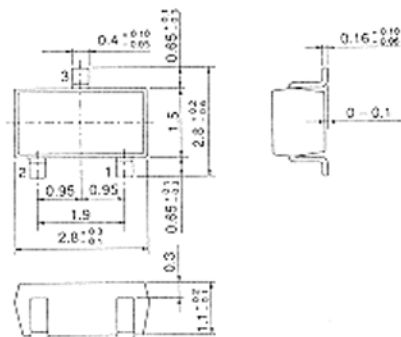


2SD1101

SILICON NPN EPITAXIAL

LOW FREQUENCY AMPLIFIER

Complementary pair with 2SB831



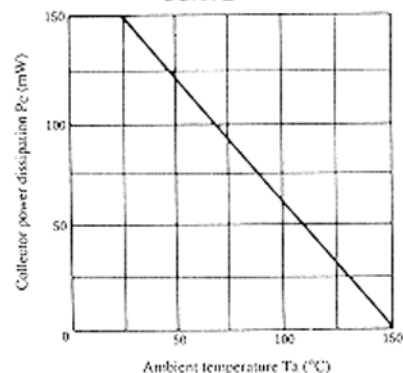
1. Emitter
 2. Base
 3. Collector
- (Dimensions in mm)

(MPAK)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SD1101	Unit
Collector to base voltage	V_{CBO}	25	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	0.7	A
Collector peak current	$i_{C(pk)}$	1	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu A, I_E = 0$	25	—	—	V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1mA, R_{BE} = \infty$	20	—	—	V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu A, I_C = 0$	5	—	—	V
Collector cutoff current	I_{CBO}	$V_{CB} = 20V, I_E = 0$	—	—	1.0	μA
DC current transfer ratio	h_{FE}^*	$V_{CE} = 1V, I_C = 0.15A^{**}$	85	—	240	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.5A, I_B = 0.05A^{**}$	—	—	0.5	V
Base to emitter voltage	V_{BE}	$V_{CE} = 1V, I_C = 0.15A^{**}$	—	—	1.0	V

* The 2SD1101 is grouped by h_{FE} as follows.

Grade	B	C
Mark	AB	AC
h_{FE}	85 to 170	120 to 240

** Pulse Test

■ See characteristic curves of 2SD467.